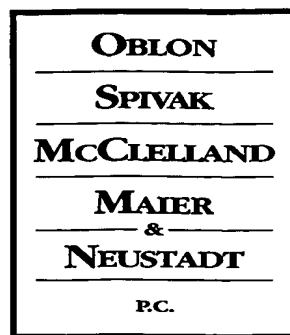




Docket No.: 240800US2S DIV

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313



RE: Application Serial No.: 10/670,529
Applicants: Norihisa ARAI
Filing Date: September 26, 2003
For: SEMICONDUCTOR DEVICE INCLUDING
IMPURITIES IN SUBSTRATE VIA MOS
TRANSISTOR GATE ELECTRODE AND GATE
INSULATION FILM
Group Art Unit: 2822
Examiner: ROSE, KIESHA L

SIR:

Attached hereto for filing are the following papers:

AMENDMENT UNDER 37 C.F.R. § 1.312

Our check in the amount of \$0.00 is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R. 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 15-0030. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. 1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

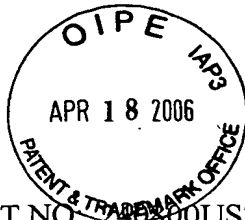

Eckhard H. Kuesters

Registration No. 28,870
Joseph Scafetta, Jr.
Registration No. 26,803
Edward Tracy
Registration No. 47,998

Customer Number

22850

(703) 413-3000 (phone)
(703) 413-2220 (fax)



DOCKET NO: 240800US2S DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF : DATE ALLOWED: JANUARY 25, 2006
NORIHISA ARAI : EXAMINER: ROSE, KIESHA L.
SERIAL NO: 10/670,529 :
FILED: SEPTEMBER 26, 2003 : GROUP ART UNIT: 2822
FOR: SEMICONDUCTOR DEVICE :
INCLUDING IMPURITIES IN
SUBSTRATE VIA MOS TRANSISTOR
GATE ELECTRODE AND GATE
INSULATION FILM

AMENDMENT UNDER 37 C.F.R. § 1.312

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

In response to the Notice of Allowance dated January 25, 2006, please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 7 of this paper.